

Supplementary Information:

Table SI-1: Overview of the fragments observed in the EI-MS (70 eV) spectra of [RE(DPDMG)₃]
 RE = Sc (1), Er (2), Y (3), Gd and Dy¹⁻²

Fragment	[RE(DPDMG) ₃]							
	Sc (1)		Er (2)		Y (3)		Dy	
	mass (m/z)	rel. int. (%)	mass (m/z)	rel. int. (%)	mass (m/z)	rel. int. (%)	mass (m/z)	rel. int. (%)
[RE(L) ₃] ³⁺ (C ₂₇ H ₆₀ N ₉ RE)	555	29	676	51	599	34	674	49
[(L) ₂ RE{(iPrN) ₂ C}] ²⁺ (C ₂₅ H ₅₄ N ₈ RE)	512	1	632	4	555	3	630	4
[RE(L) ₂] ²⁺ (C ₁₈ H ₄₀ N ₆ RE)	385	100	506	100	429	100	504	100
[(L)RE{(iPrN) ₂ CNCH ₂ }] ²⁺ (C ₁₇ H ₃₆ N ₆ RE)	369	4	490	9	413	10	488	9
[(L)RE{(iPrN) ₂ C}] ²⁺ (C ₁₆ H ₃₄ N ₅ RE)	341	73	341	73	385	46	460	48
[(L)REN(iPr)CN] ²⁺ (C ₁₃ H ₂₇ N ₅ RE)	300	6	462	45	343	12	417	14
[(L)REN(H)CN] ²⁺ (C ₁₀ H ₂₁ N ₅ RE)	257	10	377	20	301	13	376	25
[(L)RENH] ²⁺ (C ₉ H ₂₁ N ₄ RE)	230	2	351	3	274	1	349	2
[(L)RE] ²⁺ (C ₉ H ₂₀ N ₃ RE)	215	n.d.	336	4	259	n.d.	334	n.d.
[{(iPrN) ₂ CNCH ₂ }RENH] ²⁺ (C ₈ H ₁₇ N ₄ RE)	214	12	335	20	258	23	333	32
[RE{(iPrN) ₂ C}] ²⁺ (C ₇ H ₁₄ N ₂ RE)	n.d.	n.d.	n.d.	n.d.	215	3	290	8
[REN(iPr)] ²⁺ (C ₃ H ₇ NRE)	102	1	223	1	146	2	220	2

L = DPDMG = {(iPrN)₂CNMe₂}; * the peak intensity varies from 15 to 1 % in the recorded spectra; n.d. = not detected

[1] A. P. Milanov, R. A. Fischer and A. Devi, *Inorg. Chem.*, 2008, **47**, 11405-11416.

[2] A. P. Milanov, T. Thiede, A. Devi and R. A. Fischer, *J. Am. Chem. Soc.*, 2009, **131**, 17062-17063.

Fig. S1: Temperature dependent NMR data of $[\text{Sc}(\text{DPDMG})_3] \mathbf{1}$

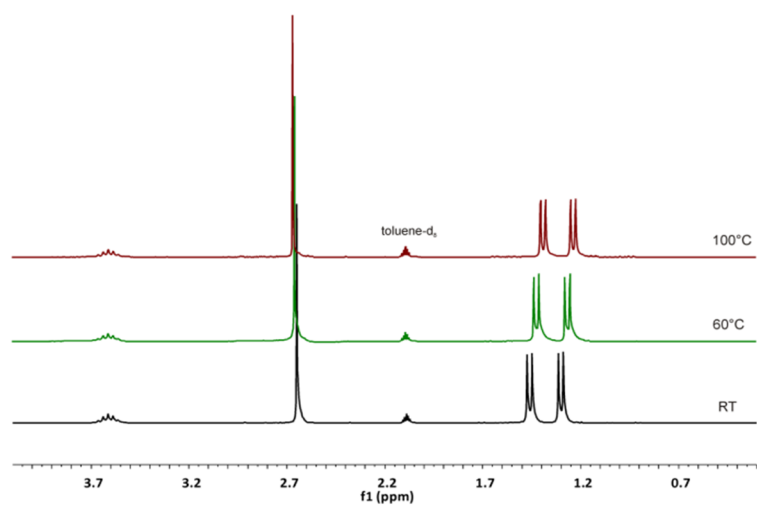


Fig. S2: Temperature dependent NMR decomposition data of $[Y(DPDMG)_3] \mathbf{3}$

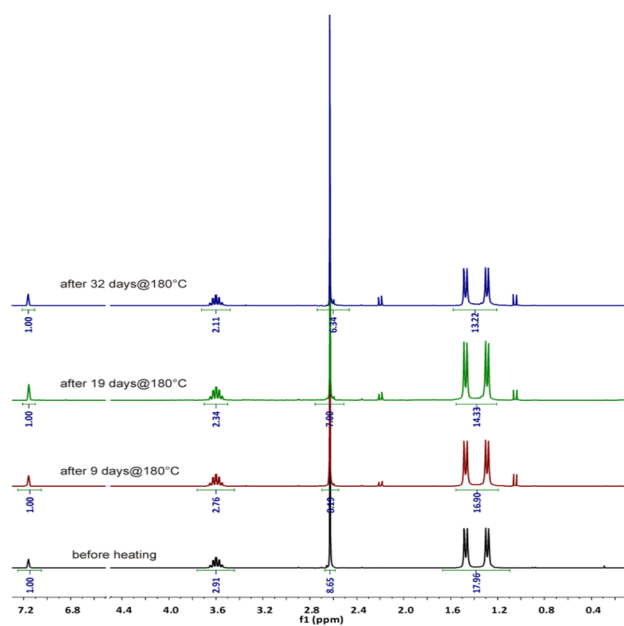


Fig. S3: SEM images of Er_2O_3 thin films deposited by MOCVD at 400 °C and 650 °C on Si(100) substrates using $[\text{Er}(\text{DPDMG})_3] \mathbf{2}$ as precursor.

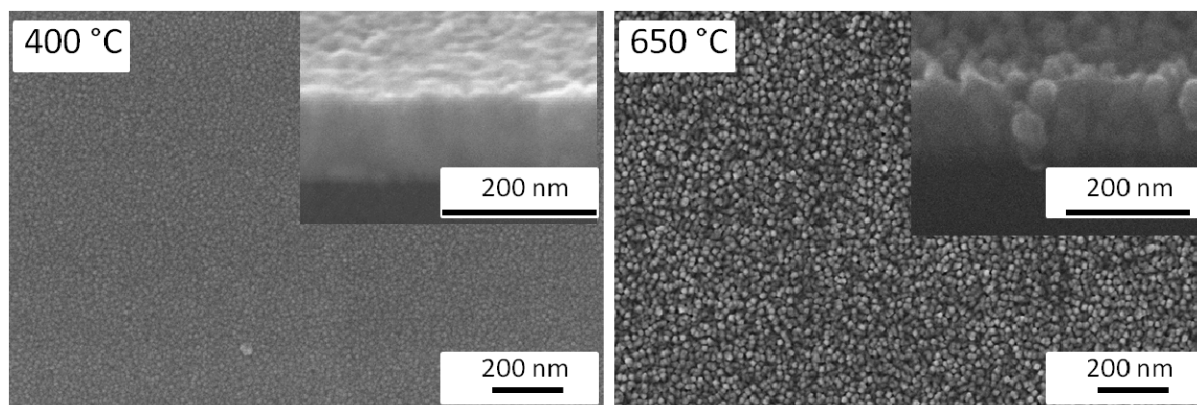


Fig. S4 AFM micrographs of Sc_2O_3 films deposited on Si(100) substrates at 400–700 °C using $[\text{Sc}(\text{DPDMG})_3] \mathbf{1}$ as precursor.

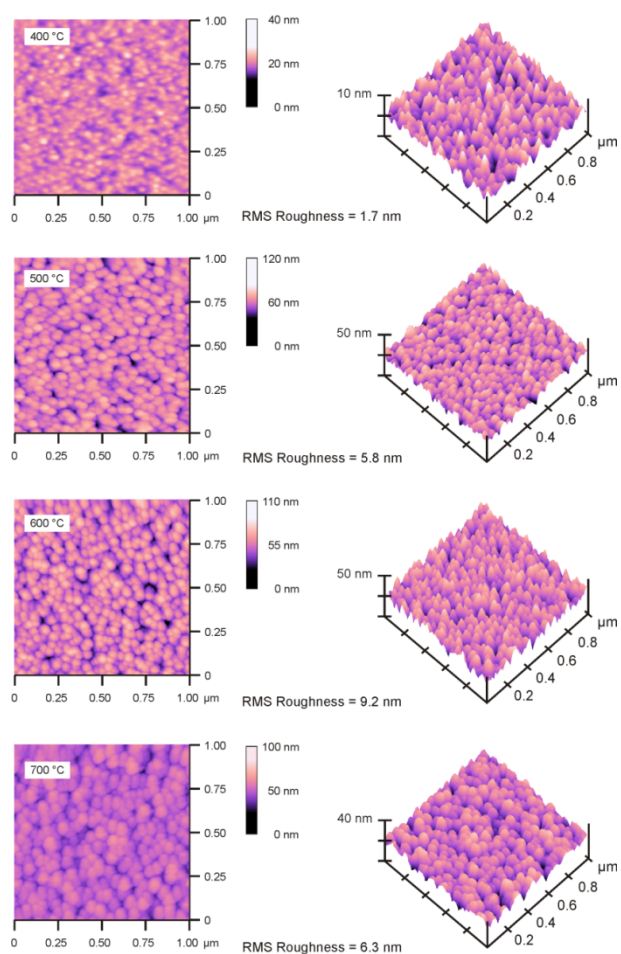


Fig. S5 AFM micrographs of Y_2O_3 films deposited on Si(100) substrates at 400–700 °C using $[\text{Y}(\text{DPDMG})_3] \mathbf{3}$ as precursor.

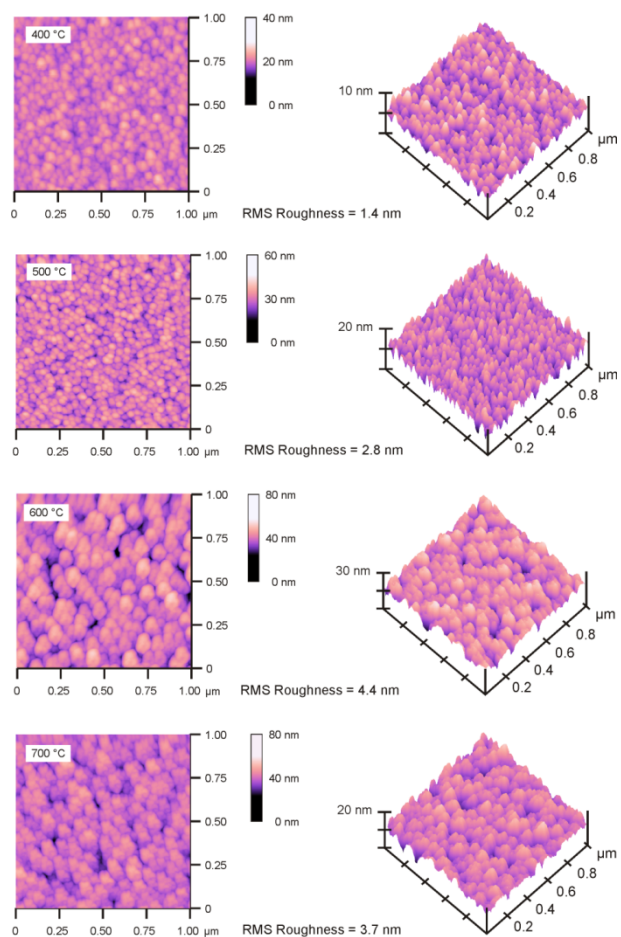


Fig. S6 EDX spectra of (a) Sc_2O_3 and (b) Y_2O_3 thin film deposited at 500 °C on Si(100) substrates using $[\text{Sc}(\text{DPDMG})_3]$ **1** and $[\text{Y}(\text{DPDMG})_3]$ **3** respectively.

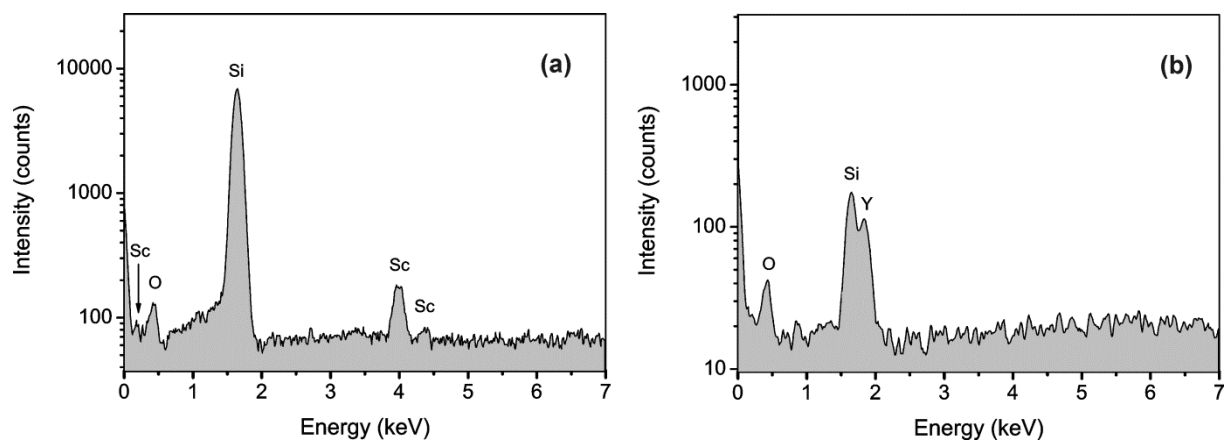


Fig. S7 RBS spectra of (a) Sc_2O_3 and (b) Y_2O_3 thin films deposited at 400 °C on glassy carbon substrates using precursors $[\text{Sc}(\text{DPDMG})_3]$ **1** and $[\text{Y}(\text{DPDMG})_3]$ **3**, respectively.

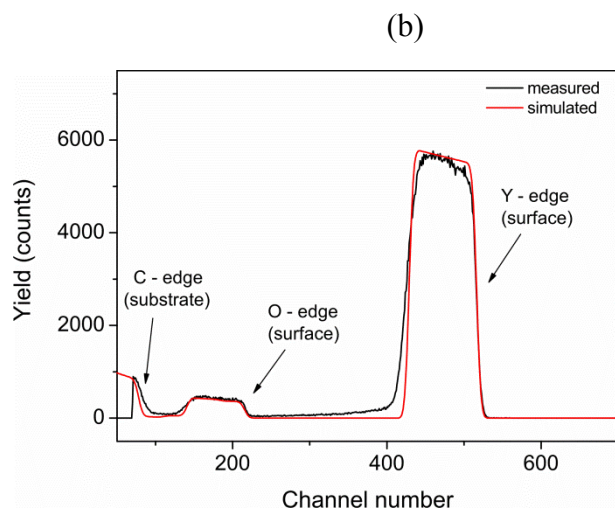
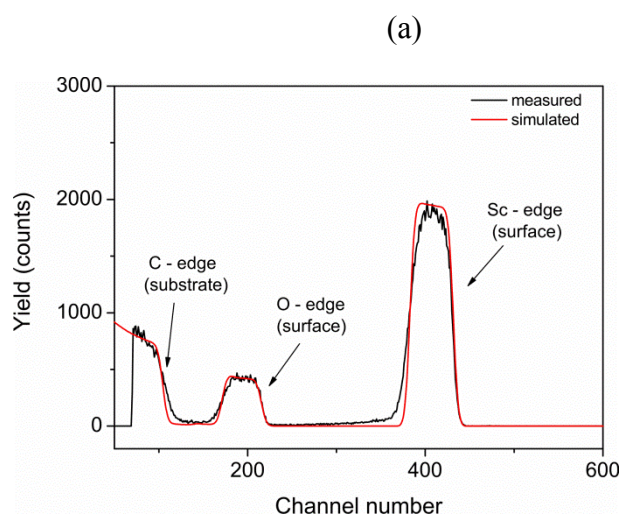


Fig. S8 (left) Background subtracted NRA (d, p-gamma) spectrum of Y_2O_3 deposited at 500 °C using **G1** ($2H^+$ beam, 0.98 MeV) (right) Summary of NRA (d, p-gamma) spectra of Y_2O_3 (measured), pure Si(100) (background), Kapton and Y_2O_3 (background subtracted). Kapton ($C_{22}H_{10}O_4N_2$) was used as standard.

